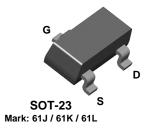


PN4091 PN4092 PN4093 MMBF4091 MMBF4092 **MMBF4093**





NOTE: Source & Drain are interchangeable

N-Channel Switch

This device is designed for low level analog switching, sample and hold circuits and chopper stabalized amplifiers. Sourced from Process 51. See J111 for characteristics.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V_{DG}	Drain-Gate Voltage	40	V	
V_{GS}	Gate-Source Voltage	- 40	V	
I _{GF}	Forward Gate Current	50	mA	
T _J ,T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C	

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max Uni		Units
		PN4091-4093	*MMBF4091-4093	
P _D	Total Device Dissipation	625	350	mW
	Derate above 25°C	5.0	2.8	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	125		°C/W
R _{θJA}	Thermal Resistance, Junction to Ambient	357	556	°C/W

^{*}Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

¹⁾ These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations

N-Channel Switch

(continued)

Vas(eff) Gate-Source Cutoff Voltage Vas = 20 V, Ib = 1.0 nA 4091 -5.0 -10 4092 -2.0 -7.0 4092 -2.0 -7.0 4092 -2.0 -7.0 4092 -2.0 -7.0 4093 -1.0 -5.0	Symbol	Parameter	Test Conditions		Min	Max	Units
VGS(off) Gate-Source Cutoff Voltage	OFF CHAF	RACTERISTICS					
VGS(off) Gate-Source Cutoff Voltage	V _{(BR)GSS}	Gate-Source Breakdown Voltage	$I_G = 1.0 \mu A, V_{DS} = 0$		- 40		V
Mose	V _{GS(off)}	Gate-Source Cutoff Voltage	$V_{DS} = 20 \text{ V}, I_{D} = 1.0 \text{ nA}$	4091	- 5.0	- 10	V
Drain-Gate Leakage Current						_	V
V _{DG} = 20 V, I _S = 0, T _A = 150°C	Ingo	Drain-Gate Leakage Current		4093	1.0		pA
Drain Cutoff Leakage Current	-DGO	Drain Gate Loakage Garrent		С			nA
V _{DS} = 20 V, V _{GS} = -6.0 V 4093 400 r V _{DS} = 20 V, V _{GS} = -12 V, V _{GS} = -12 V, V _{GS} = -12 V, V _{GS} = -20 V, V _{GS} = -20 V, V _{GS} = -8.0 V, V _{GS} = 20 V, V _{GS} = -8.0 V, V _{GS} = 20 V, V _{GS} = -6.0 V, V _{GS} = -6.0 V, V _{GS} = -6.0 V, V _{GS} = 20 V, V _{GS} = -6.0 V, V _{GS} = -6.0 V, V _{GS} = 0 V _{DS} = 20 V, V _{GS} = 0 V _{DS} = 20 V, V _{GS} = 0 V _{DS} = 20 V, V _{GS} = 0 V _{DS} = 20 V, V _{GS} = 0 V _{DS} = 20 V, V _{GS} = 0 V _{DS} = 20 V, V _{GS} = 0 V _{DS} = 20 V, V _{GS} = 0 V _{DS} = 20 V, V _{GS} = 0 V _{DS} = 20 V, V _{GS} = 0 V _{DS} = 20 V, V _{GS} = 0 V _{DS} = 20 V, V _{GS} = 0 V _{DS} = 20 V, V _{GS} = 2	I _{D(off)}	Drain Cutoff Leakage Current	V _{DS} = 20 V, V _{GS} = -12 V			200	pА
Vos = 20 V, Vgs = -12 V,							pΑ
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$				4093		200	pA
Vos = 20 V, Vos = -8.0 V, Vos = -8.0 V, Vos = 20 V, Vos = -8.0 V, Vos = 20 V, Vos = -8.0 V, Vos = 20 V, Vos = -6.0 V, Vos = 20 V, Vos = -6.0 V, Vos = -7.0				4001		400	nA
T _A = 150°C 4092 4000 r V _{DS} = 20 V, V _{GS} = -6.0 V, 4093 4000 r T _A = 150°C 4093 30 4000 r T _A = 150°C 4093 30 7 T _A = 150°C 4093 4092 15 T _A = 150°C 4091 4092 4093 409				4031			
Ta = 150°C 4093 400 FT				4092		400	nA
DON CHARACTERISTICS			$V_{DS} = 20 \text{ V}, V_{GS} = -6.0 \text{ V},$			400	
Description Section			T _A = 150°C	4093		400	nA
ID = 2.5 mA, VGS = 0 4093 0.2 ID = 1.0 mA, VGS = 0 4091 30 4092 50 4093 80 SMALL-SIGNAL CHARACTERISTICS Indicates I		ŭ	$I_D = 6.6 \text{ mA}, V_{GS} = 0$	4092 4093 4091	15		mA mA V V
Drain-Source On Resistance ID = 1.0 mA, VGS = 0 4091 30 4092 50 4093 80 4093 40 40 40 40 40 40 40 4						-	v
SMALL-SIGNAL CHARACTERISTICS T _{ds(on)} Drain-Source On Resistance V _{DS} = V _{GS} = 0, f= 1.0 kHz 4091 4092 50 4093 80 80	ľDS(on)	Drain-Source On Resistance					Ω
SMALL-SIGNAL CHARACTERISTICS r _{ds(on)} Drain-Source On Resistance V _{DS} = V _{GS} = 0, f= 1.0 kHz 4091 4092 4093 4093 4093 4093 4093 4093 4093 4093	. DO(011)					50	Ω
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$			4	4093		80	Ω
				4092		50	ΩΩ
	C.	Input Canacitance					Ω pF
		<u>'</u>		12			pF
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Orss	Neverse Transfer Gapacitance	VG5 = 20 V, 1 = 1.0 WHZ			0.0	Pi
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	<u>SWITCHII</u>	NG CHARACTERISTICS					
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	t _{on}	Turn-On Time	I _{D(on)} = 12 mA	4091			ns
t_{off} Turn-Off Time $V_{\text{GS(off)}} = 12 \text{ V}$ 4091 40			. ,	4092			ns
V GS(011) = 12 V				4093			ns
1 - 1 - 1 - 1 - 1 - 1 - 1 - 1 - 1 - 1 -	t _{off}	Turn-Off Time					ns
VGS(0II) - 0.0 V +032			00(0)	4092			ns ns

^{*}Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 1.0%

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